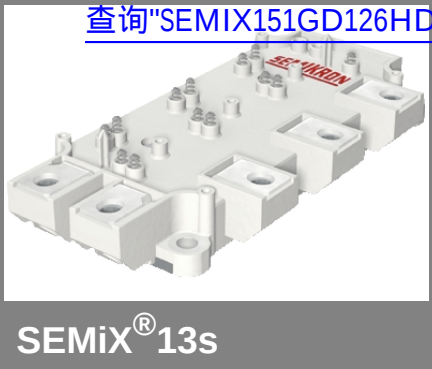


SEMiX 151GD126HDs



Trench IGBT Modules

SEMiX 151GD126HDs

Preliminary Data

Features

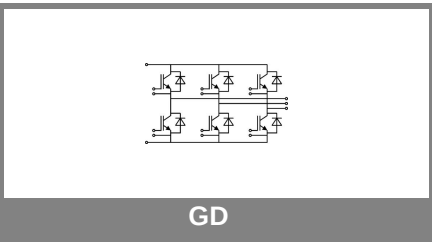
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to $T_C=125^{\circ}C$ max.



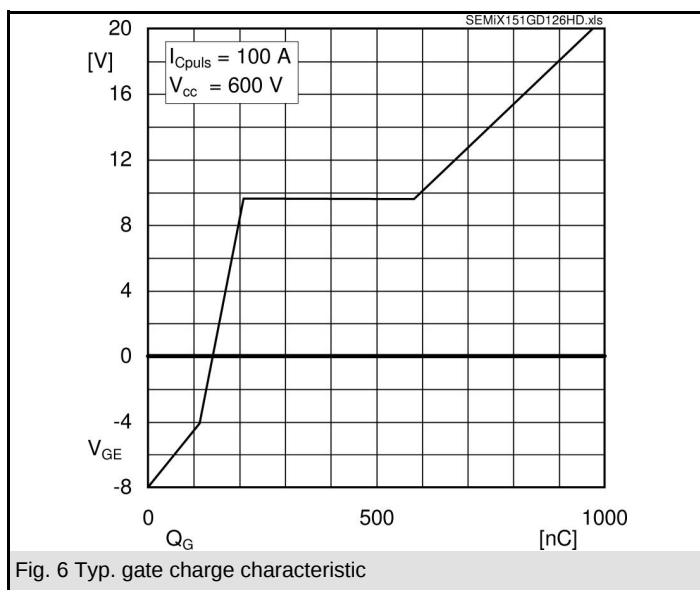
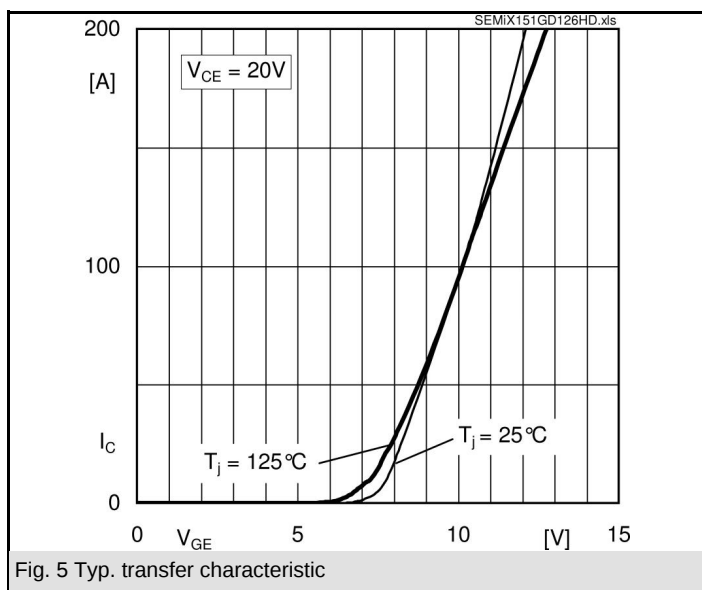
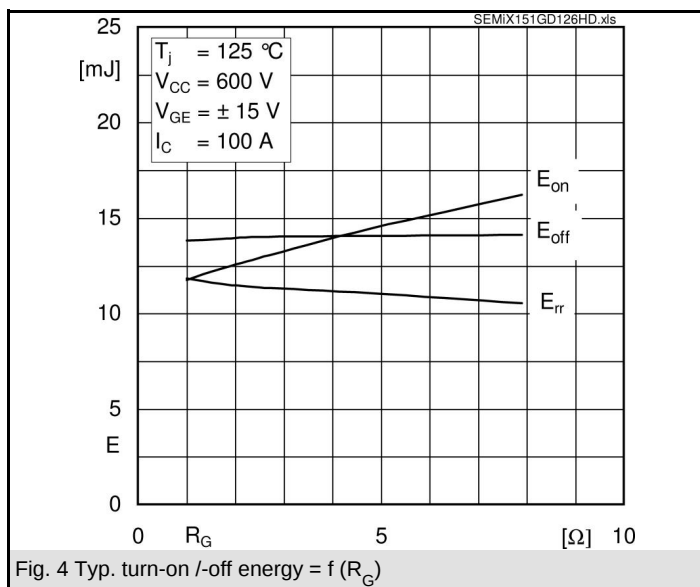
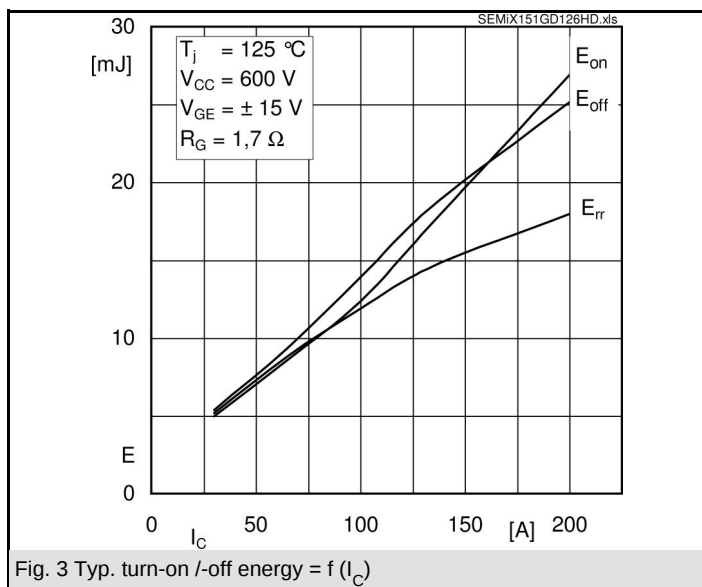
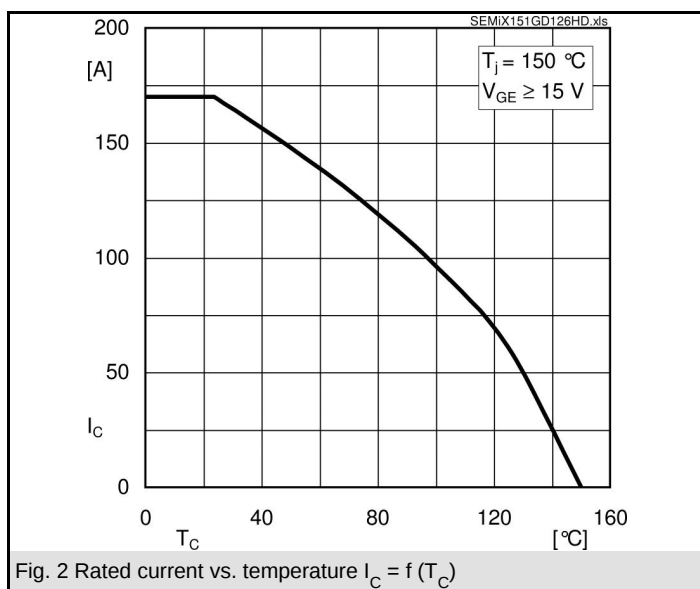
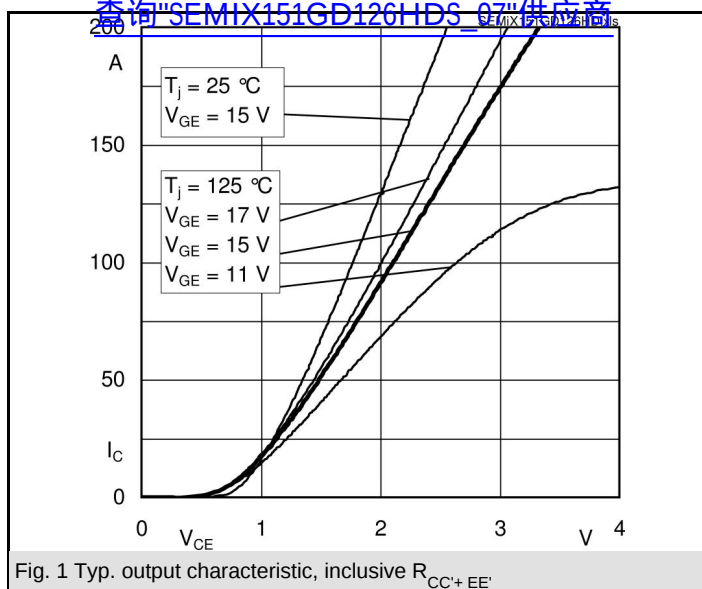
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Characteristics					
Symbol	Conditions		min.	typ.	max. Units
Inverse Diode					
V _F = V _{EC}	I _{Fnom} = 100 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,6	1,8 V
		T _j = 125 °C _{chiplev.}		1,6	1,8 V
V _{F0}		T _j = 25 °C		1	1,1 V
		T _j = 125 °C		0,8	0,9 V
r _F		T _j = 25 °C		6	7 mΩ
		T _j = 125 °C		8	9 mΩ
I _{RRM}	I _{Fnom} = 100 A	T _j = 125 °C		125	A
Q _{rr}	di/dt = 2900 A/μs			26	μC
E _{rr}	V _{GE} = -15 V; V _{CC} = 600 V			11,5	mJ
R _{th(j-c)D}	per diode			0,36	K/W
Module					
L _{CE}				20	nH
R _{CC'+EE'}	res., terminal-chip	T _{case} = 25 °C		0,7	mΩ
		T _{case} = 125 °C		1	mΩ
R _{th(c-s)}	per module			0,04	K/W
M _s	to heat sink (M5)		3		5 Nm
M _t	to terminals (M6)		2,5		5 Nm
w					350 g
Temperature sensor					
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)			0,493±5%	kΩ
B _{100/125}	R(T)=R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K]			3550±2%	K

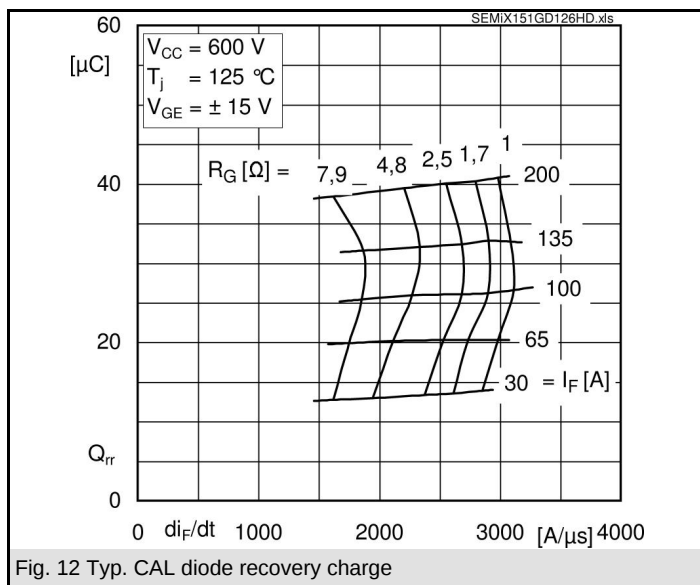
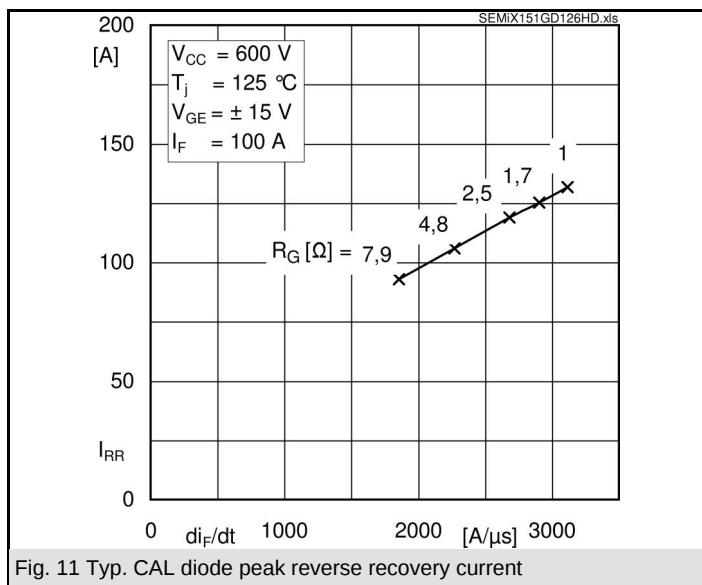
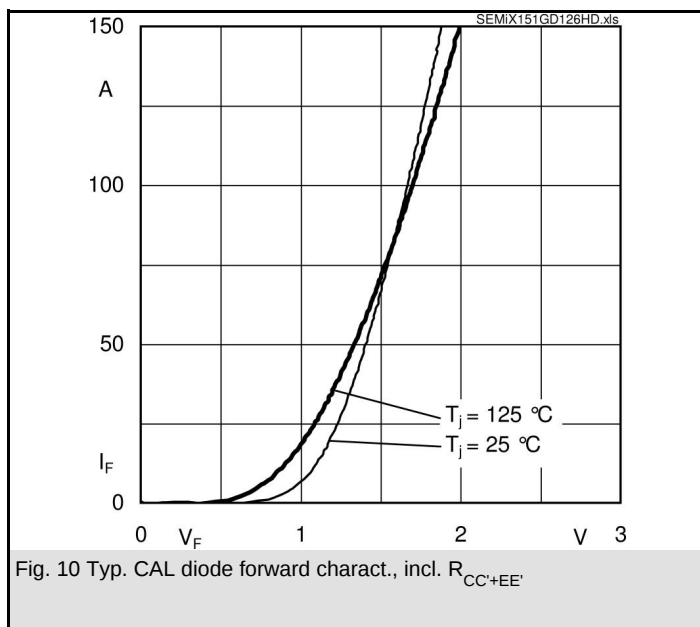
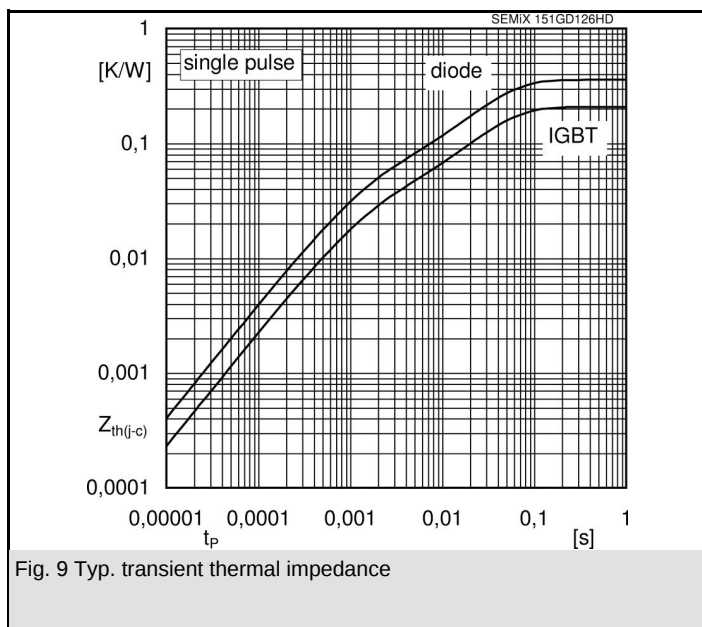
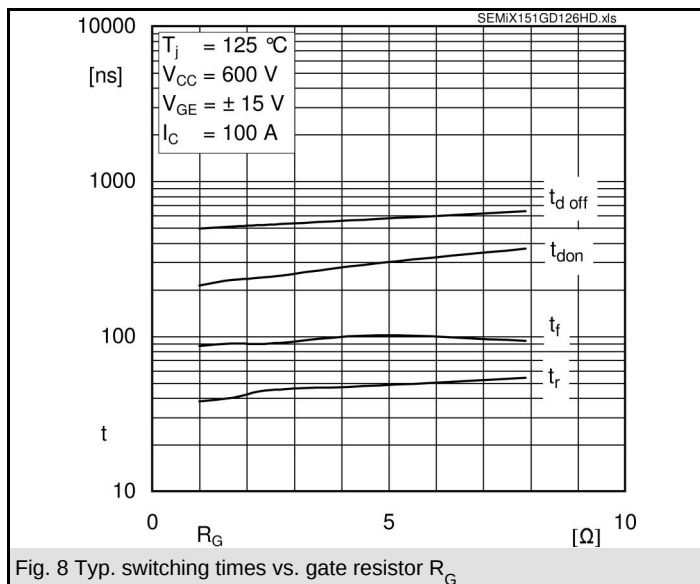
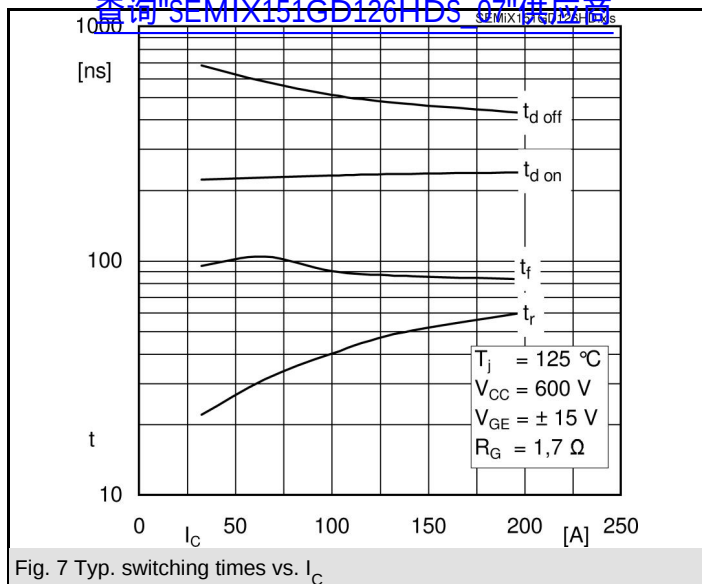
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

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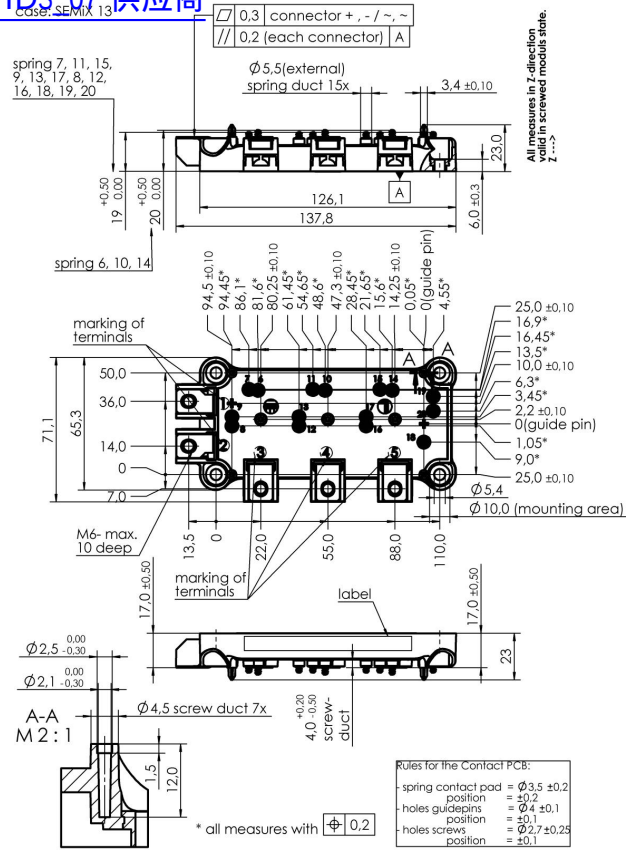


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Case SEMiX 13s

